Amendments to the Specification

Please replace Paragraph No. **0015** at page 5 with the following amended paragraph:

[0015] In a third embodiment of the present invention, the method comprises the steps of purifying a purge gas containing water at a concentration between about 100 ppm and about 2% moisture with the overall mixture having a molecular contaminant concentration of less than 1 ppb, introducing the purified purge gas into an interior portion of the device, contacting at least a portion of the surfaces with the purified purge gas, producing a contaminated purge gas by transferring a portion of the molecular contaminants from the surfaces into the purified purge gas, and removing the purified purge gas from said device. The method further comprises the step of continuing the preceding steps until the contaminant concentration ~~is~~ of the contaminated purge gas is decreased to a desired level, preferably below 100 ppt contaminant on a volume basis.

Please replace Paragraph No. **0041** at pages 8-9 with the following amended paragraph:

[0041] The present invention provides a potential new paradigm for the purging contaminants from silicon or stainless steel surfaces. It is proposed that in addition to kinetic energy, non-inert molecules such as oxygen and water, may exhibit a chemical effect. This is where oxygen or water, because of their electronegative and polarized nature respectively, has a strong affinity for the electropositive surface of the silicon or stainless steel and forms a weakly bound absorbed thin layer. Once a collision leads to desorption, re-adsorption of the contaminant species is hindered by the oxygen thin layer. In the case of water which forms stronger surface bonds, the thin layer is even more rigid and prevents readsorption. Since nitrogen is less electronegative than oxygen, the thin layer is very weakly bound and less effective. In addition, N_2 is lighter than O_2; therefore, it may have less of a kinetic effect. This proposed mechanism is not a limitation of the instant invention. Purification and cleaning of components and apparatuses is preferably carried out at temperatures between ambient temperatures (about 20°C) to about 50°C. Cleaning may be carried out at higher temperatures, up to 100°C or even 150°C. The temperature used is dependent upon a number of criteria wellknown to those skilled in the art including, but not limited to, the thermal tolerance of the components to be cleaned (*e.g.*, foups are typically made of plastic), the volatility of the potential contaminants at various temperatures and the temperatures that the components will be subjected to during the manufacturing process. In one embodiment, the temperature is ambient temperature up to 150°C. In one preferred embodiment, the temperature is in the range of 80°C to 100°C. In another embodiment, the temperature is in the range of 100°C to 150°C when the components being cleaned are stainless steel.